

Technical Data

TRANSISTOR

maximum ratings

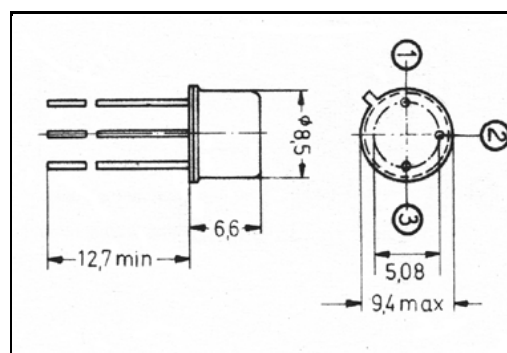
Voltage, Collector to Base (VCBO)	120.0	V	NO.	BSX47-10
Voltage, Collector to Emitter (VCE)	80.0	V	TYPE	NPN
Voltage, Emitter to Base (VEBO)	7.0	V		
Collector Current (IC)	1.0	A		
Base Current (IB)	0.2	A	CASE	TO-39
Max. Power Dissipation (PT) at TC = 25 °C	5.0	W		
Max. Thermal Resistance (Rth J-C)	35.0	°C/W		
Max. Junction Temperature (TJ)	200.0	°C		

PERFORMANCE CHARACTERISTICS at $T_c = 25^\circ\text{C}$, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	BVCEO	IC = 50.0 mA (1)	80.0	-	V
2.	BVCES	ICE = 100.0 μA	120.0	-	V
3.	BVEBO	IEB = 100.0 μA	7.0	-	V
4.	ICES	VCE = 80.0 V	-	30.0	nA
5.	ICES	VCE = 80.0 V, TA = 150.0 °C	-	10.0	μA
6.	IEBO	VEB = 5.0 V	-	10.0	nA
7.	hFE	IC = 100.0 μA , VCE = 1.0 V (1)	15.0	-	-
8.	hFE	IC = 100.0 mA, VCE = 1.0 V (1)	63.0	160.0	-
9.	hFE	IC = 500.0 mA, VCE = 1.0 V (1)	25.0	-	-
10.	hFE	IC = 1.0 A, VCE = 1.0 V (2)	20.0	-	-
11.	VCE(SAT)	IC = 500.0 mA, IB = 25.0 mA (1)	-	0.9	V
12.	VBE(ON)	IC = 500.0 mA, VCE = 1.0 V (1)	-	1.5	V
13.	fT	VCE = 10.0 V, IC = 50.0 mA, f = 20.0 MHz	50.0	-	MHz
14.	Cobo	VCB = 10.0 V, f = 1.0 MHz	-	15.0	pF
15.	tON	IC = 100.0 mA, IB = 5.0 mA	-	200.0	ns
16.	tOFF	IC = 100.0 mA, IB = 5.0 mA	-	850.0	ns
17.					
18.					
19.					
20.					

Notes (1) pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
(2) typ. value / pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

DIMENSIONS
in mm



Marking BSX47-10
Customer GENERAL PURPOSE